

/ Descriptions

TO-126F

NPN

Silicon NPN transistor in a TO-126F Plastic Package.

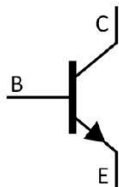
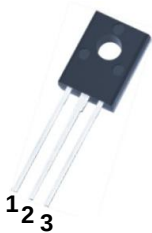
/ Features

BD140

Complement to BD140.

/ Applications

Medium power linear and switching applications.

/ Equivalent Circuit**/ Pinning**

PIN1 Emitter

PIN 2 Collector

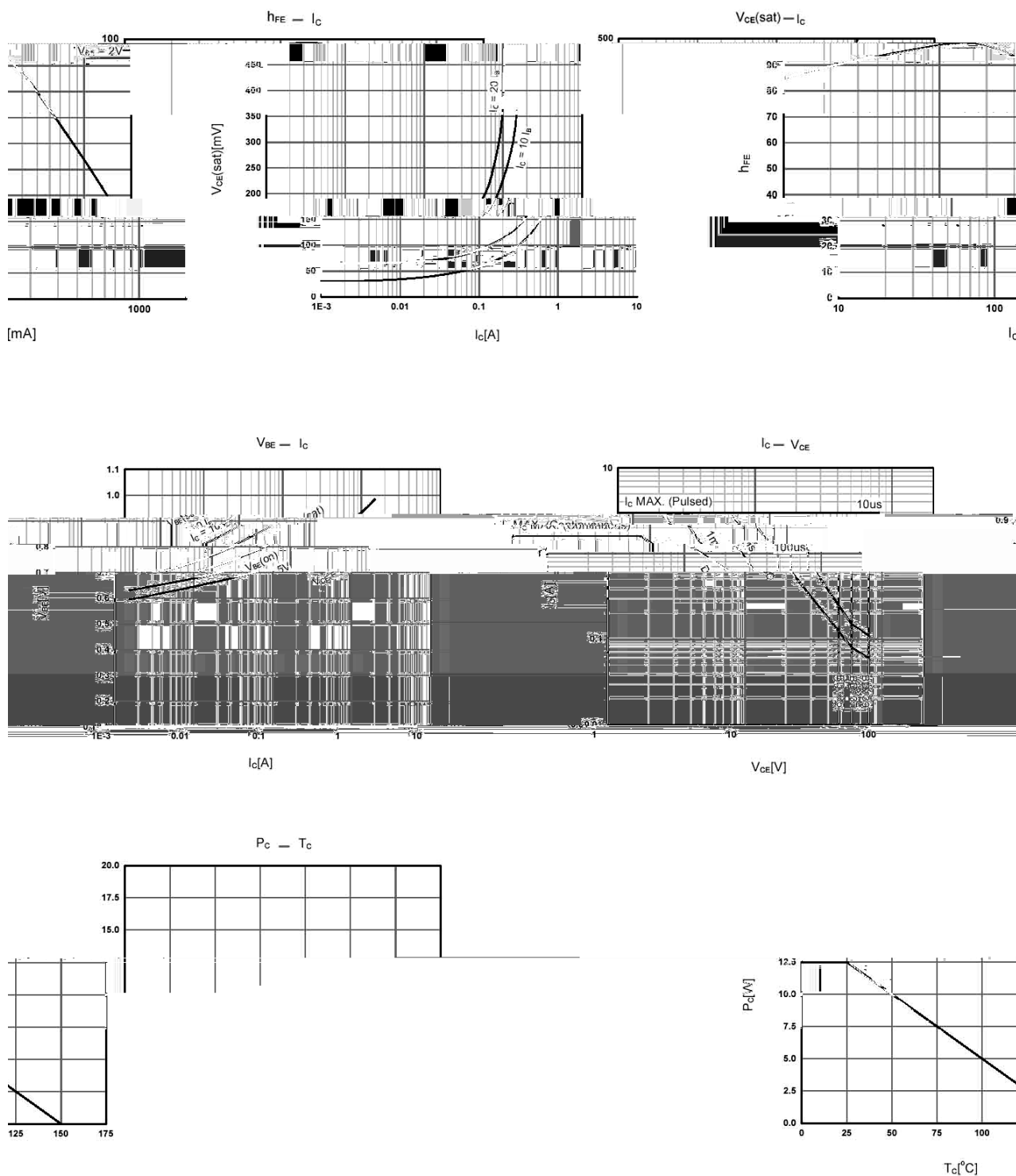
PIN 3 Base

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	6	10	16	25
h_{FE} Range	40~100	63~160	100~250	160~400

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.5	A
Collector Current – Continuous	I_{CP}	3.0	A
Base Current – Continuous	I_B	0.5	A
Collector Power Dissipation	P_C	1.25	W
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	12.5	W
Junction Temperature	T_J	150	

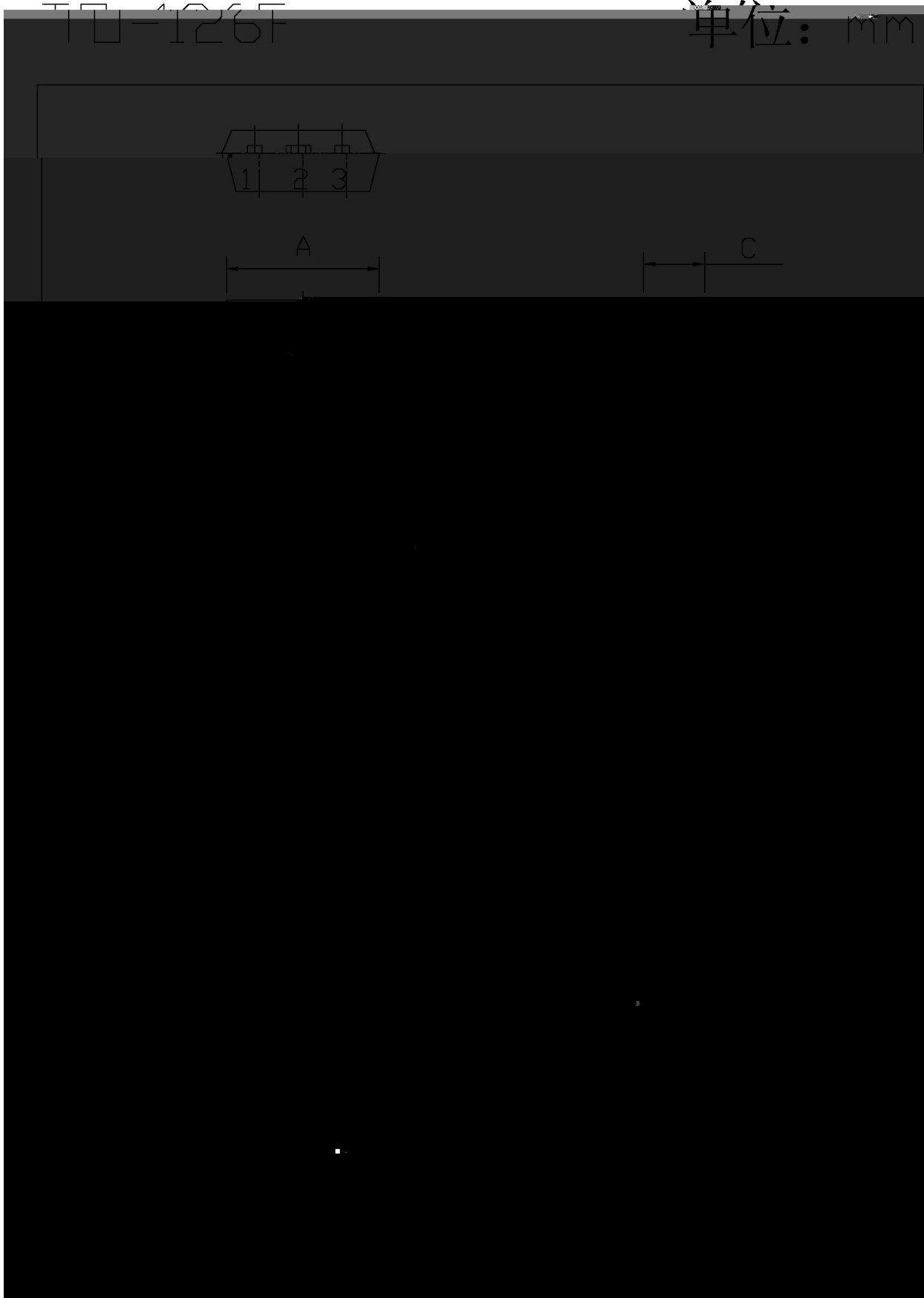
/ Electrical Characteristic Curve



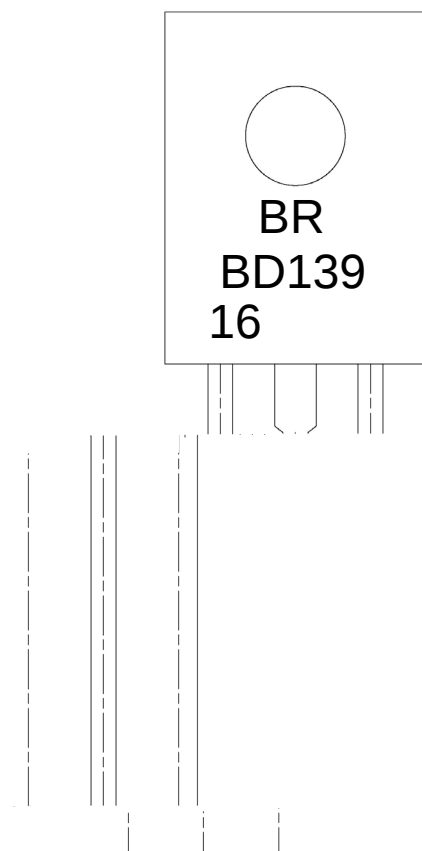
/ Package Dimensions

TU-126F

单位: mm



/ Marking Instructions



BR

BD139

16: h_{FE}

Note:

BR: Company Code

BD139: Product Type.

16: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

255±5

5±0.5sec;

2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3

5 11.1086 0 TD0 Tc0.03bd7j/TT4 1 Tf1 0 TD-0.0002 Tc0.0024 Tw6[0.5s7.1(T)50.6/4743 -